Icemos Technology Ltd Product Specification 1000.673501 Issue Date 11 December 2020 15

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I Part Number	Customer	

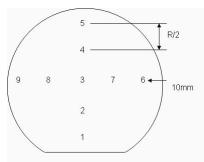
Category	Parameter		Specification	Measurement Method
OverallWafer	1.0	Diameter	100.00 +/- 0.20 mm	
	2.0	Primary Flat Orientation	{110} +/- 1.0 degree	Wafer Vendor
	3.0	Primary Flat Length	32.50 +/- 2.50 mm	Wafer Vendor
	4.0	Secondary Flat Orientation	none	Wafer Vendor
	5.0	Overall Thickness	501.00 +/- 11.00 μm	ADE, 100%
	6.0	Total Thickness Variation (TTV)	<5.00μm	Guaranteed by Process
	7.0	Bow	<80.00μm	ADE to ASTM F534, 100%
	8.0	Warp	<80.00μm	
	9.0	Edge Chips	0	Bright Light, 100% (note 2)
	10.0	Edge Exclusion	5mm	
HandleSilicon	11.0	Handle Growth Method	CZ	Wafer Vendor
	12.0	Handle Orientation	{100} +/- 1.0 degree	Wafer Vendor
	13.0	Handle Thickness	350.00 +/- 10.00 μm	ADE, 100%
	14.0	Handle Doping Type	P	Wafer Vendor
	15.0	Handle Dopant	Boron	Wafer Vendor
	16.0	Handle Resistivity	1 - 30 Ohmcm	Wafer Vendor
	17.0	Backside Finish	Polished with Oxide and Lasermark	Guaranteed by process
BuriedOxide	18.0	Oxide Type	Thermal	
	19.0	Oxide Thickness	10,000.00 +/- 500.00 A	Nanospec centre point, 4%
	20.0	Oxide formed on	Handle and / or Device wafer	Graranteed by process
DeviceSilicon	21.0	Device Growth Method	CZ	Wafer Vendor
	22.0	Device Orientation	{100} +/- 1.0 degree	Wafer Vendor
	23.0	Nominal Thickness	150.00 +/- 0.50 μm	Filmetrics 9pt, 100%
	24.0	Distance to device silicon edge from wafer edge	< 2.0 mm	Guaranteed by process
	25.0	Depth into handle variation within wafer	< 100um	Guaranteed by process
	26.0	Device Doping Type	P	Wafer Vendor
	27.0	Device Dopant	Boron	Wafer Vendor
	28.0	Device Resistivity	1 ~ 30 Ohm cm	Wafer Vendor
	29.0	Voids	none	Bright Light, 100% (note 2)
	30.0	Scratches	0	Bright Light, 100% (note 2)
	31.0	Haze	none	Bright Light, 100% (note 2)
	32.0	LPD Count	< 30 > 0.3um	Tencor Particle counter
	33.0	Device Field Oxidation	10,000.00 +/- 500.00 A	Nanospec centre point, 4%

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Part Number		Customer			
Category	Parameter	Specification		Me	asurement Method
Shipping Details	Wafer per box :	Max 25			
	Packaging:	Taped Polypropylene Wafer Box Empak, Ultrapak, 100.00mm Antistatic Double Bagging			
	Lot Shipment Data	Device Thickness Bow / Warp Data Handle and SOI Thickness			
Explanatory Notes	1. Microscope inspec	tion performed using microscope scar	ı as below. 5x object	tive.	
	2. All bright light ins	pections performed exclude all wafer	area outside the edge	e exclusion define	d in Overall

2. All bright light inspections performed exclude all wafer area outside the edge exclusion defined in Overal Wafer, Edge Exclusion. High intensity bright lamp inspection as per ASTM F523.

3. 9 point measurement are as shown in the diagram below:



Additional Information